

# RJK5020DPK

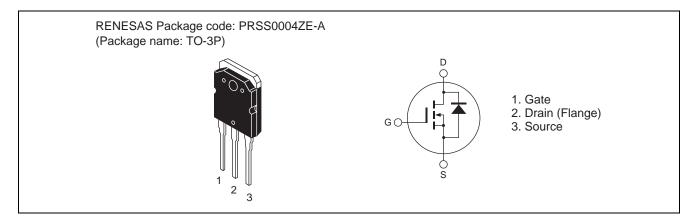
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1263-0300 Rev.3.00 Jun 30, 2010

#### **Features**

- Low on-resistance
- Low leakage current
- High speed switching

#### **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item  | Symbol                       | Ratings     | Unit |
|---|------------------------------|-------------|------|
| Drain to source voltage                     | $V_{DSS}$                    | 500         | V    |
| Gate to source voltage                      | $V_{GSS}$                    | ±30         | V    |
| Drain current                               | I <sub>D</sub>               | 40          | Α    |
| Drain peak current                          | I <sub>D (pulse)</sub> Note1 | 120         | А    |
| Body-drain diode reverse drain current      | I <sub>DR</sub>              | 40          | Α    |
| Body-drain diode reverse drain peak current | I <sub>DR</sub> (pulse)      | 120         | Α    |
| Avalanche current                           | I <sub>AP</sub> Note3        | 12.5        | Α    |
| Avalanche energy                            | E <sub>AR</sub> Note3        | 8.6         | mJ   |
| Channel dissipation                         | Pch Note2                    | 200         | W    |
| Channel to case thermal impedance           | θch-c                        | 0.625       | °C/W |
| Channel temperature                         | Tch                          | 150         | °C   |
| Storage temperature                         | Tstg                         | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu s, \, duty \, cycle \leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

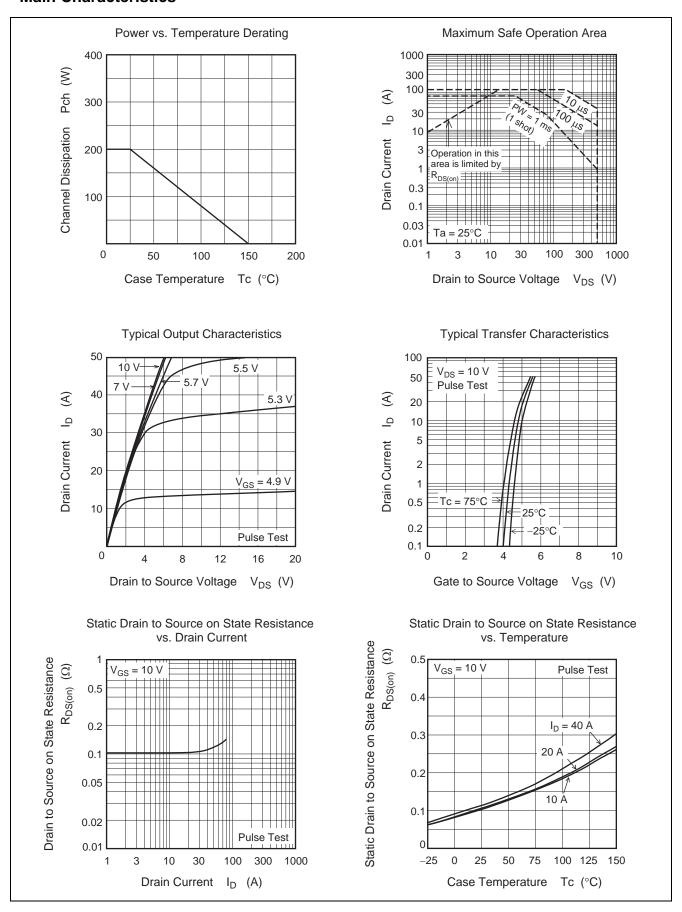
# **Electrical Characteristics**

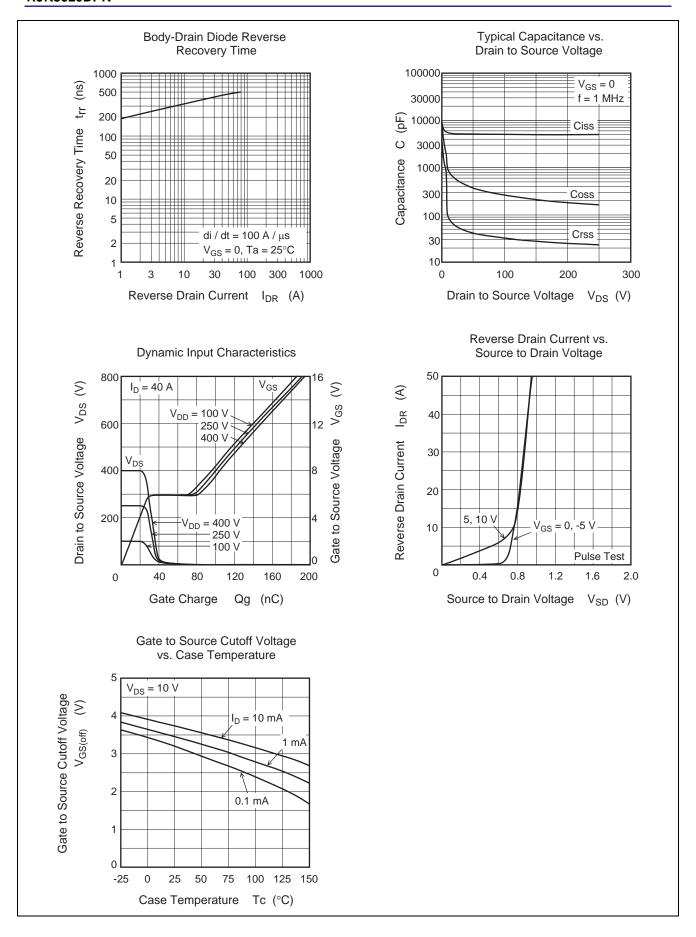
 $(Ta = 25^{\circ}C)$ 

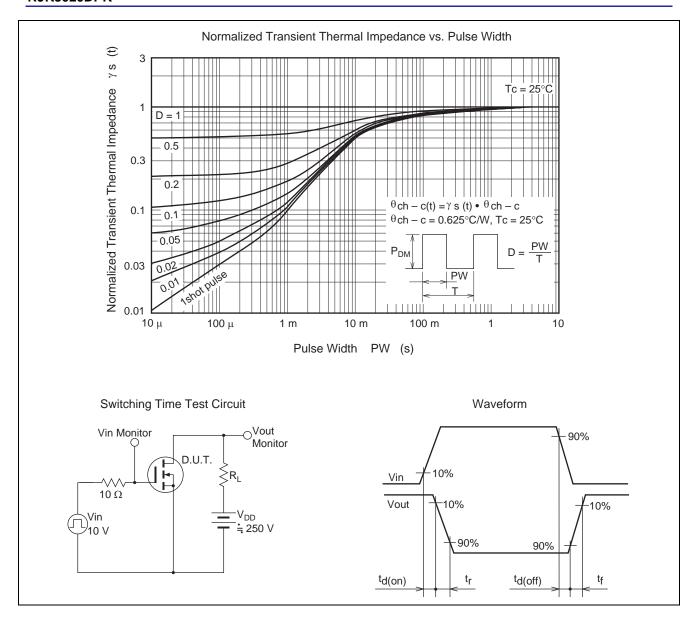
| Item                                       | Symbol              | Min | Тур   | Max   | Unit | Test conditions   |
|--|---------------------|-----|-------|-------|------|---|
| Drain to source breakdown voltage          | $V_{(BR)DSS}$       | 500 |       | _     | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$   |
| Zero gate voltage drain current            | I <sub>DSS</sub>    |     |       | 1     | μΑ   | $V_{DS} = 500 \text{ V}, V_{GS} = 0$  |
| Gate to source leak current                | I <sub>GSS</sub>    |     | _     | ±0.1  | μΑ   | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$   |
| Gate to source cutoff voltage              | $V_{GS(off)}$       | 3.0 | _     | 4.5   | V    | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$                                     |
| Static drain to source on state resistance | R <sub>DS(on)</sub> | l   | 0.102 | 0.118 | Ω    | $I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$                        |
| Input capacitance                          | Ciss                |     | 5150  | _     | pF   | V <sub>DS</sub> = 25 V  |
| Output capacitance                         | Coss                | _   | 525   | _     | pF   | V <sub>GS</sub> = 0<br>f = 1 MHz  |
| Reverse transfer capacitance               | Crss                | _   | 55    | _     | pF   |   |
| Turn-on delay time                         | t <sub>d(on)</sub>  | _   | 52    | _     | ns   | $I_D = 20 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 12.5 \Omega$ $Rg = 10 \Omega$ |
| Rise time                                  | t <sub>r</sub>      | _   | 115   | _     | ns   |   |
| Turn-off delay time                        | $t_{d(off)}$        | _   | 180   | _     | ns   |   |
| Fall time                                  | t <sub>f</sub>      | _   | 125   | _     | ns   |   |
| Total gate charge                          | Qg                  | _   | 126   | _     | nC   | V <sub>DD</sub> = 400 V<br>V <sub>GS</sub> = 10 V<br>I <sub>D</sub> = 40 A        |
| Gate to source charge                      | Qgs                 | _   | 26    | _     | nC   |   |
| Gate to drain charge                       | Qgd                 | _   | 54    | _     | nC   |   |
| Body-drain diode forward voltage           | $V_{DF}$            | _   | 0.90  | 1.50  | V    | $I_F = 40 \text{ A}, V_{GS} = 0^{\text{Note4}}$                                   |
| Body-drain diode reverse recovery time     | t <sub>rr</sub>     | _   | 450   | _     | ns   | $I_F = 40 \text{ A}, V_{GS} = 0$<br>di <sub>F</sub> /dt = 100 A/ $\mu$ s          |

Notes: 4. Pulse test

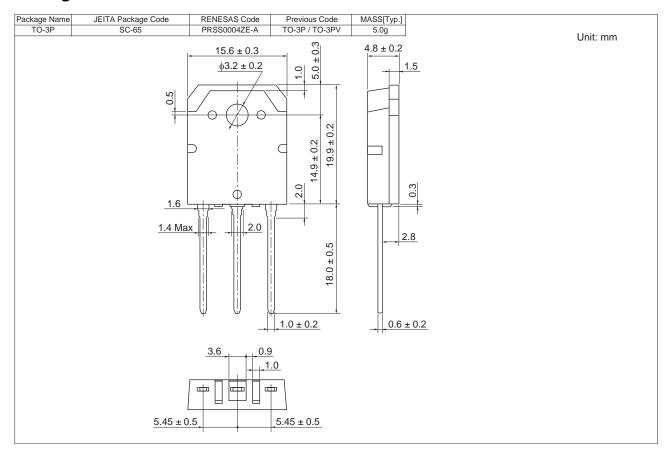
#### **Main Characteristics**







### **Package Dimensions**



# **Ordering Information**

| Part No.         | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK5020DPK-00-T0 | 360 pcs  | Box (Tube)         |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Electronics America Inc. 2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A. Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

เพลายอย อเชียงเทเชง **ทยายู nong Limited** Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong Tel: +852-2866-9318, Fax: +852-2866-9022/9044

Renesas Electronics Taiwan Co., Ltd.

7F, No. 363 Fu Shing North Road Taipei, Taiwar Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.

1 harbourFront Avenue, #06-10, keppel Bay Tower, Singapore 098632
Tel: +65-6273-0200, Fax: +65-6278-8019
Renesas Electronics Malaysia Sdn.Bhd.

เพราะสอน เมราะเพราะเพราะสามารถ งสท.**ษกด.** Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd. 11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea Tel: 482-2-588-3737, Fax: 482-2-588-5141

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